Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	60	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 5) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	1.6 1.2	A
	t<10s	T_A = +25°C T_A = +70°C	I_D	2.0 1.6	A
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	2.3 1.8	A
	t<10s	T_A = +25°C T_A = +70°C	I_D	2.9 2.3	A
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	1.5	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I_{DM}	10	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	0.7	W
	T_A = +70°C		0.4	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	183	°C/W
	t<10s		115	
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	1.3	W
	T_A = +70°C		0.8	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	94	°C/W
	t<10s		61	
Thermal Resistance, Junction to Case		$R_{\theta JC}$	39	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 60V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	1	—	3	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	92	140	mΩ	V_{GS} = 10V, I_D = 1.8A
			115	170		V_{GS} = 4.5V, I_D = 1.3A
Forward Transfer Admittance	$\|Y_{fs}\|$	—	2.2	—	S	V_{DS} = 15V, I_D = 1.8A
Diode Forward Voltage	V_{SD}	—	0.75	1.0	V	V_{GS} = 0V, I_S = 0.45A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	315	—	pF	V_{DS} = 40V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	18	—		
Reverse Transfer Capacitance	C_{rss}	—	16	—		
Gate Resistnace	R_g	—	0.65	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge (V_{GS} = 10V)	Q_g	—	8.6	—	nC	V_{DS} = 30V, I_D = 1.8A
Total Gate Charge (V_{GS} = 5V)	Q_g	—	4.1	—		
Gate-Source Charge	Q_{gs}	—	1.0	—		
Gate-Drain Charge	Q_{gd}	—	1.7	—		
Turn-On Delay Time	$t_{D(on)}$	—	2.6	—	ns	V_{DS} = 30V, V_{GS} = 10V, R_G = 6.0Ω, I_D = 1.8A
Turn-On Rise Time	t_r	—	3.6	—		
Turn-Off Delay Time	$t_{D(off)}$	—	16.3	—		
Turn-Off Fall Time	t_f	—	2.7	—		
Reverse Recovery Time	t_{rr}	—	16.8	—	ns	I_F = 1.8A, di/dt =100A/µs
Reverse Recovery Charge	Q_{rr}	—	9.0	—	nC	

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1in. square copper plate.
7 .Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

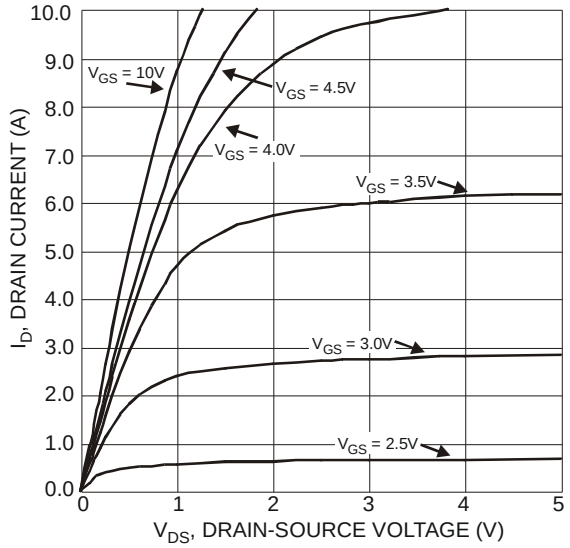


Figure 1 Typical Output Characteristic

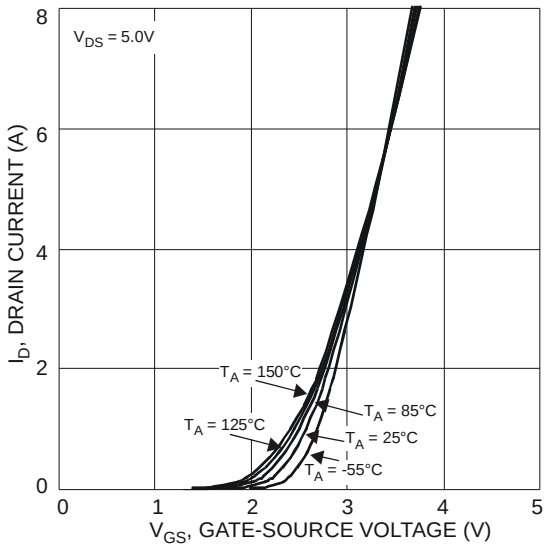


Figure 2 Typical Transfer Characteristics

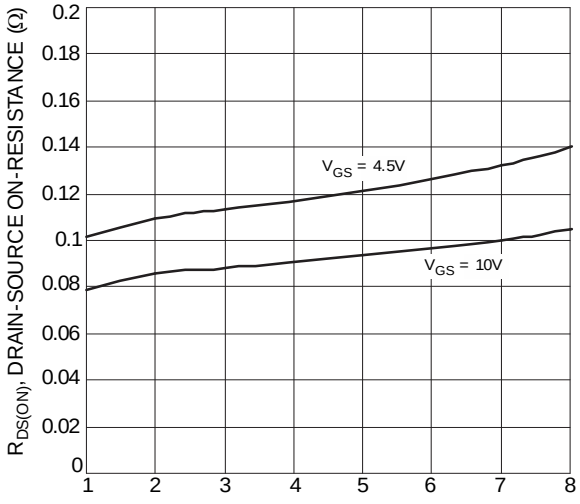


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

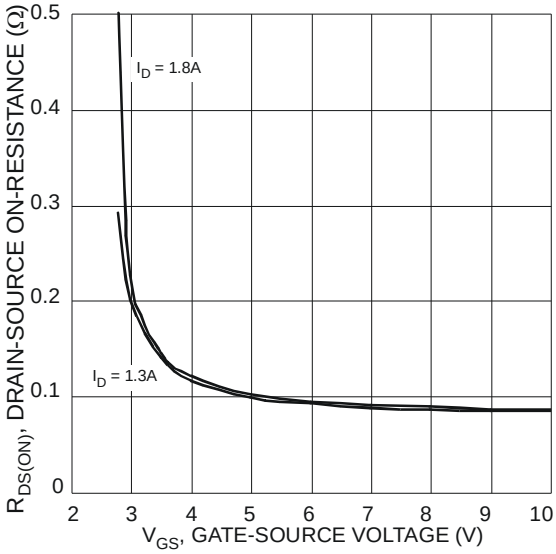


Figure 4 Typical Drain-Source On Resistance vs. Gate-Source Voltage

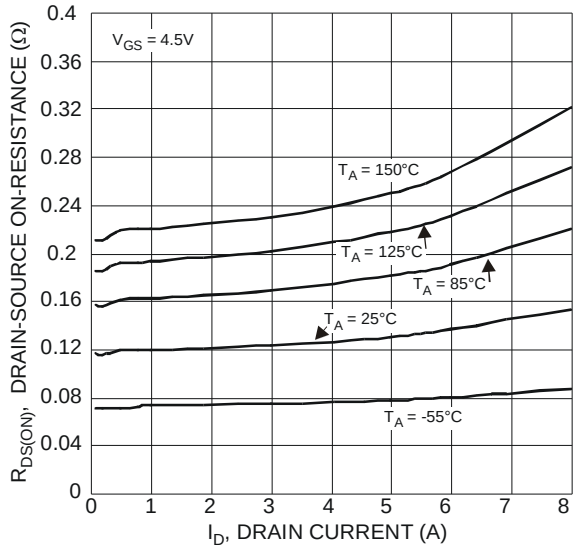


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

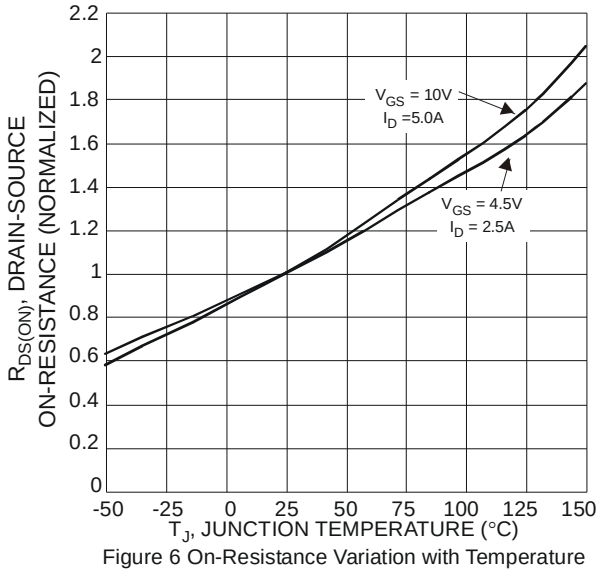


Figure 6 On-Resistance Variation with Temperature

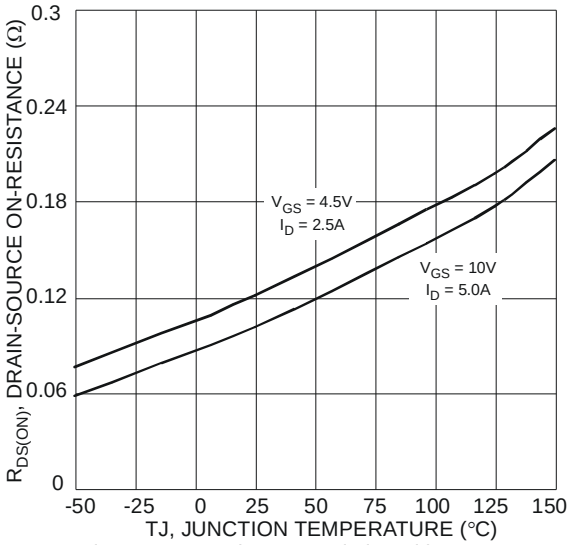


Figure 7 On-Resistance Variation with Temperature

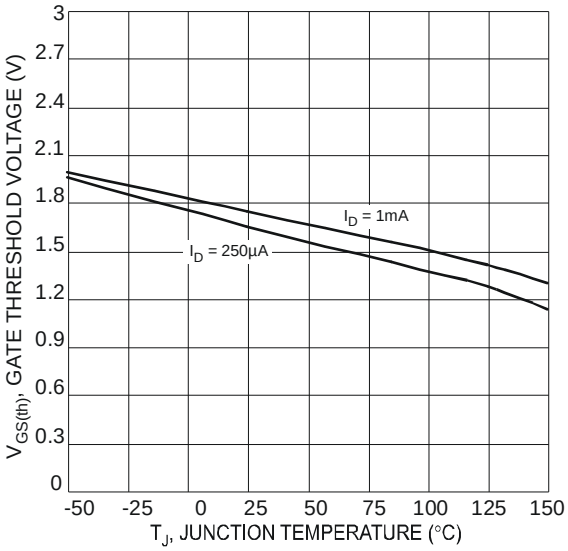


Figure 8 Gate Threshold Variation vs. Ambient Temperature

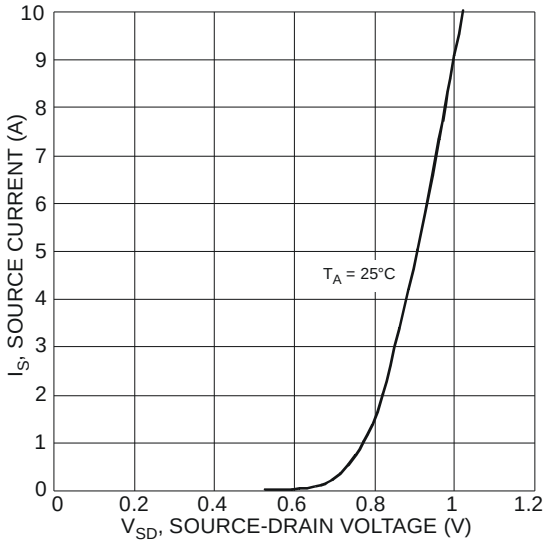


Figure 9 Diode Forward Voltage vs. Current

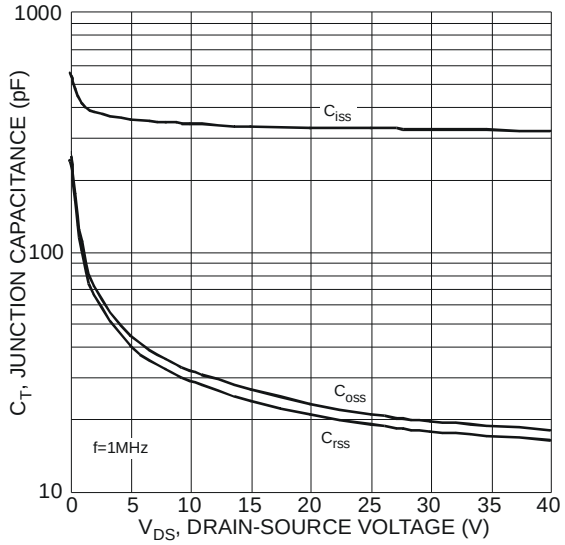


Figure 10 Typical Junction Capacitance

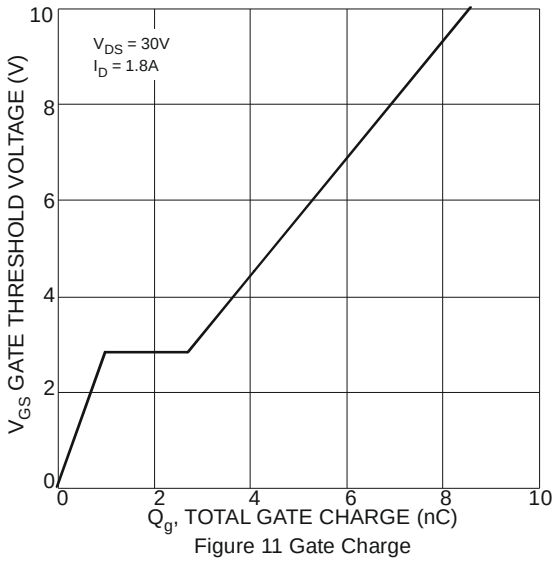


Figure 11 Gate Charge

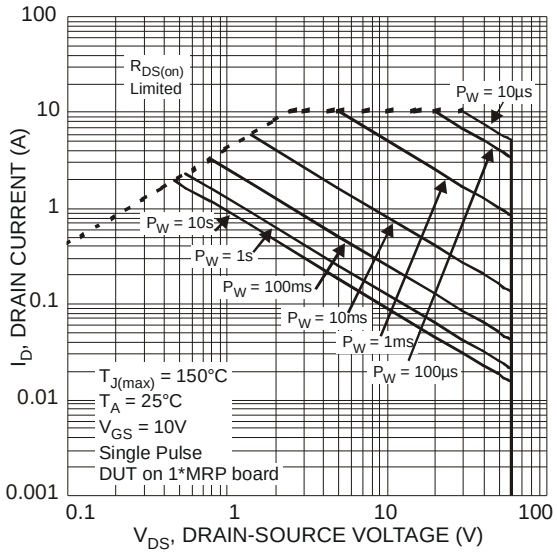


Figure 12 SOA, Safe Operation Area

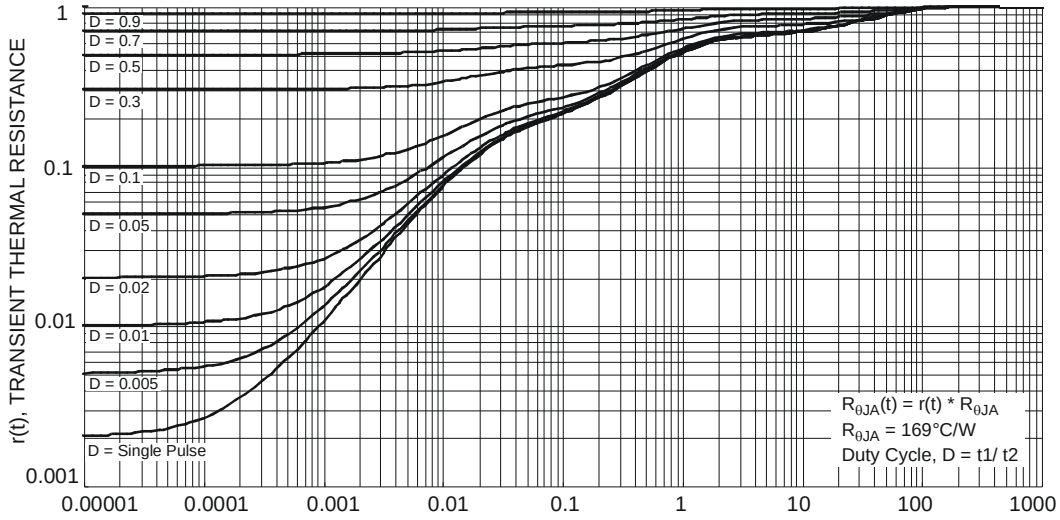
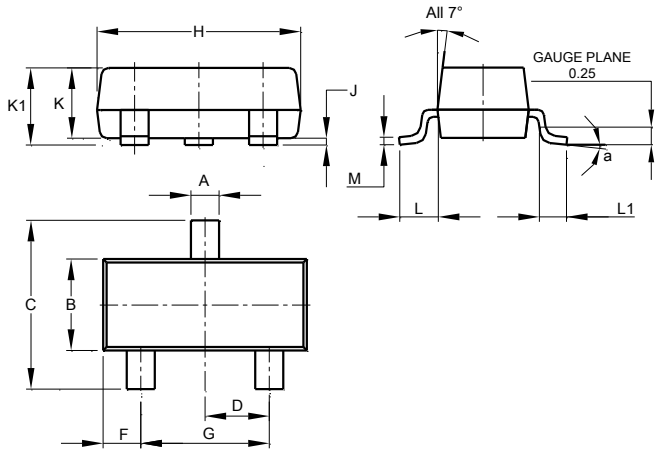


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

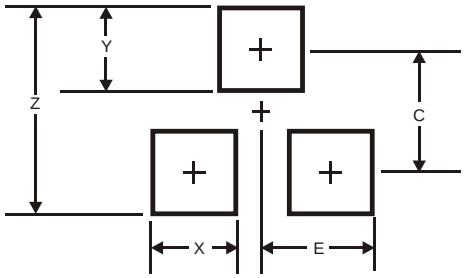
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT23			
Dim	**Min**	**Max**	**Typ**
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
α	8°		
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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